



## Description

### JMT P-channel Enhancement Mode Power MOSFET

#### Features

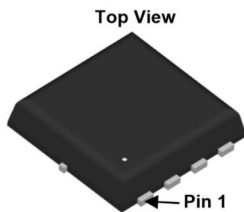
- $V_{DS} = -30V$ ,  $I_D = -15A$   
 $R_{DS(ON)} < 14m\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} < 24m\Omega @ V_{GS} = -4.5V$
- Advanced Trench Technology
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead free product is acquired

#### Application

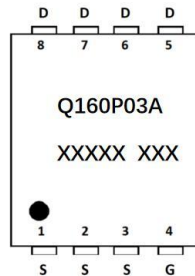
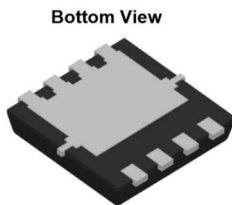
- PWM Applications
- Load Switch
- Power Management



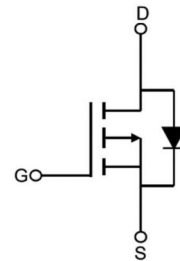
*100% UIS TESTED!*  
*100% ΔVds TESTED!*



PDFN3x3-8L



Marking and pin Assignment



Schematic Diagram

## Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
Q160P03A	JMTQ160P03A	TAPING	PDFN3x3-8L	13inch	5000	50000

## Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
$V_{DSS}$	Drain-Source Voltage	-30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ C$	-15
		$T_C = 100^\circ C$	-9.8
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>	-60	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>note2</sup>	40	mJ
$P_D$	Power Dissipation $T_C = 25^\circ C$	5.4	W
$R_{\theta JA}$	Thermal Resistance, Junction to Case	23	$^\circ C/W$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> = -250μA	-30	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -30V, V <sub>GS</sub> =0V,	-	-	-1	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1.0	-1.6	-2.5	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>Note3</small>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -10A	-	11	14	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5A	-	17	24	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = -15V, V <sub>GS</sub> =0V, f=1.0MHz	-	2070	-	pF
C <sub>oss</sub>	Output Capacitance		-	273	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	246	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = -15V, I <sub>D</sub> = -5A, V <sub>GS</sub> = -10V	-	22	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	4	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	5.8	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> = -15V, I <sub>D</sub> = -10A, V <sub>GS</sub> =-10V, R <sub>GEN</sub> =2.5Ω	-	9	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	13	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	48	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	20	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	-15	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-60	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> = -15A	-	-0.8	-1.2	V
trr	Reverse Recovery Time	T <sub>J</sub> =25°C,	-	64	-	ns
Qrr	Reverse Recovery Charge	V <sub>DD</sub> = -24V, I <sub>F</sub> =-2.8A, dI/dt=-100A/μs	-	25	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

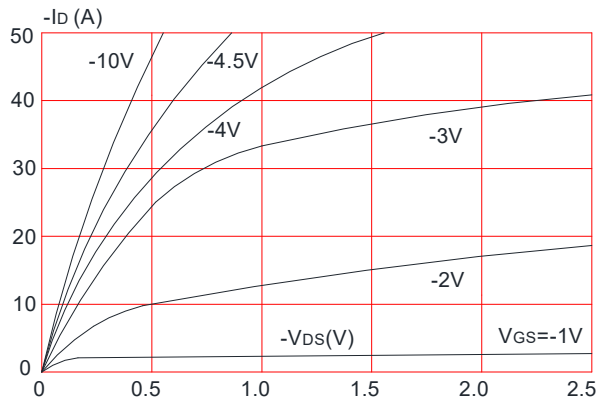
2. EAS condition: T<sub>J</sub>=25°C, V<sub>GS</sub>=10V, R<sub>G</sub>=25Ω, L=0.5mH, I<sub>AS</sub>=-12.7A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

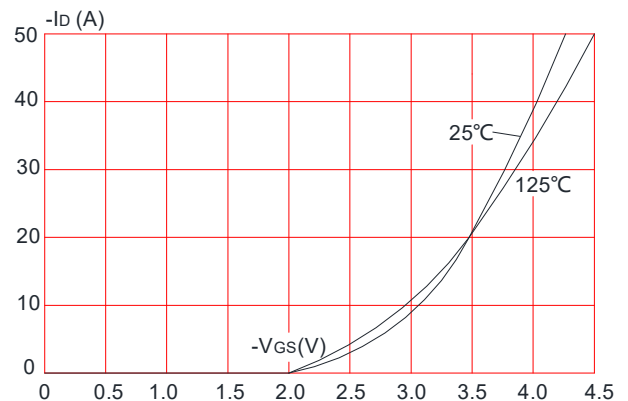


## Typical Performance Characteristics

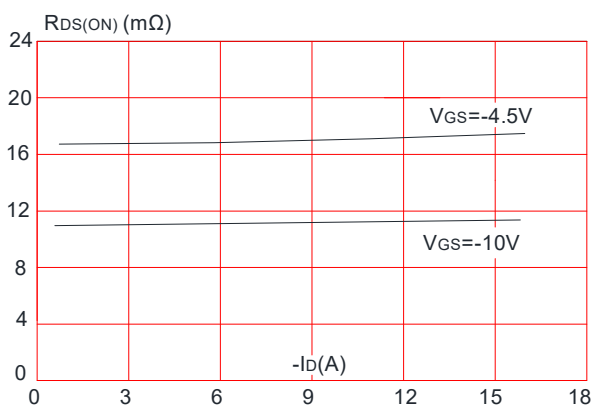
**Figure 1: Output Characteristics**



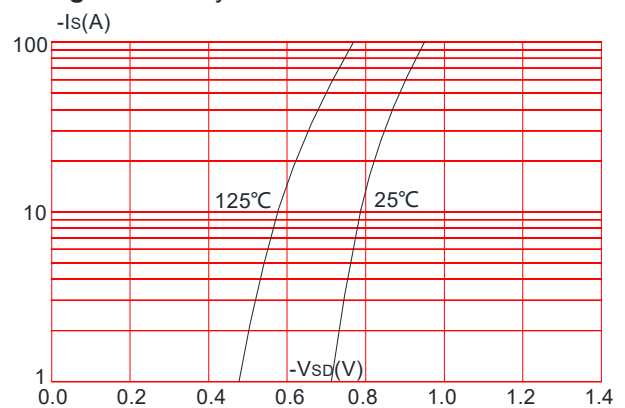
**Figure 2: Typical Transfer Characteristics**



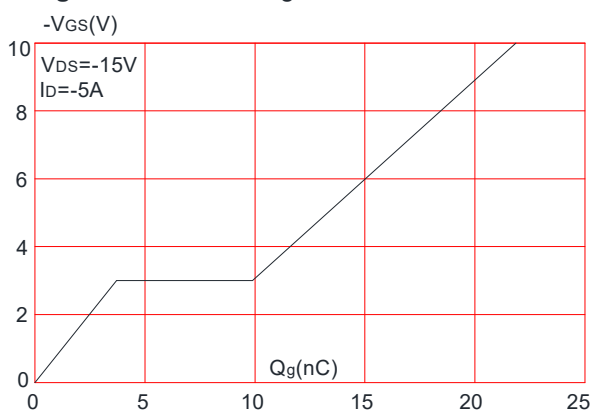
**Figure 3: On-resistance vs. Drain Current**



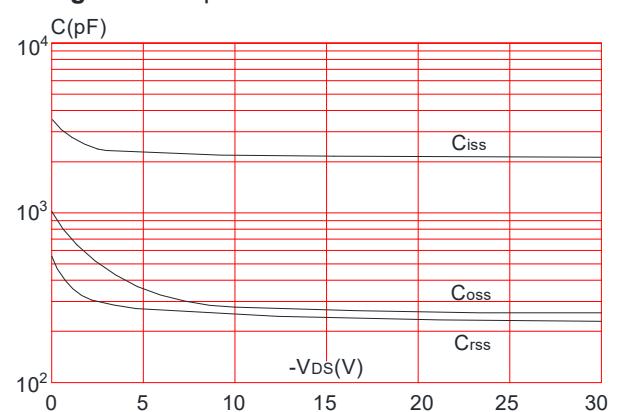
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**



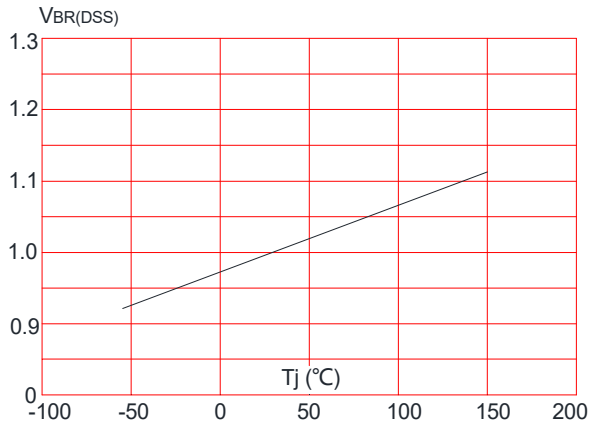
**Figure 6: Capacitance Characteristics**



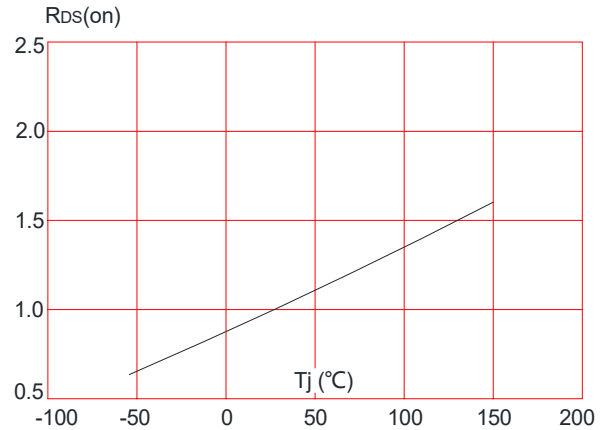


# JMTQ160P03A

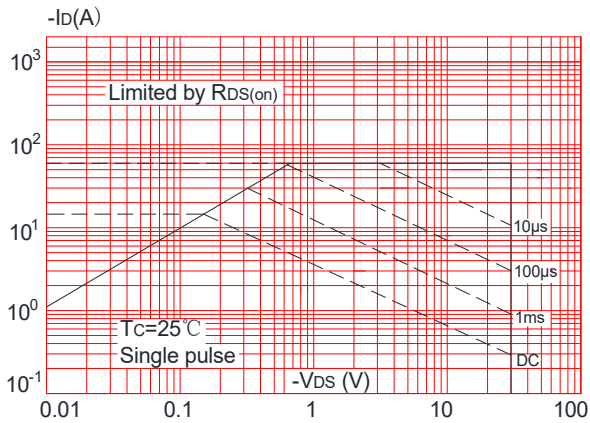
**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**



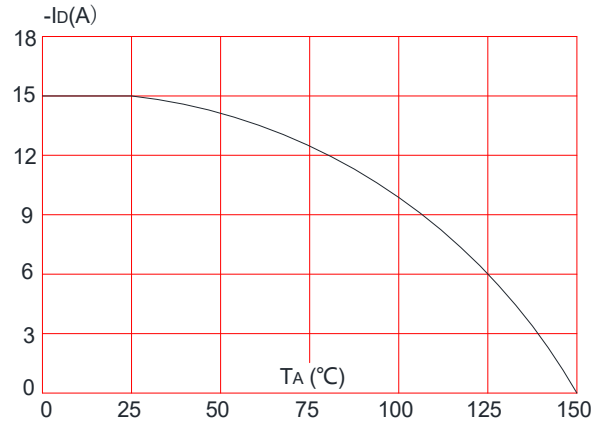
**Figure 8: Normalized on Resistance vs. Junction Temperature**



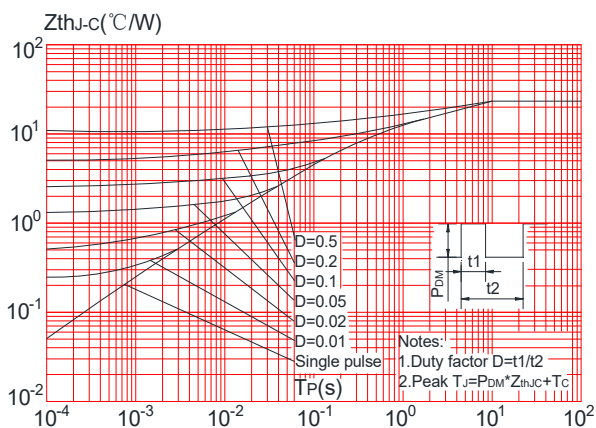
**Figure 9: Maximum Safe Operating Area**



**Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature**

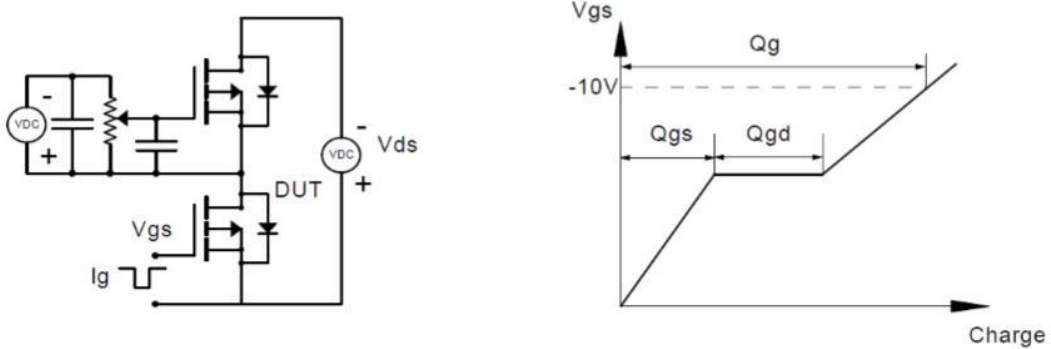


**Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case**

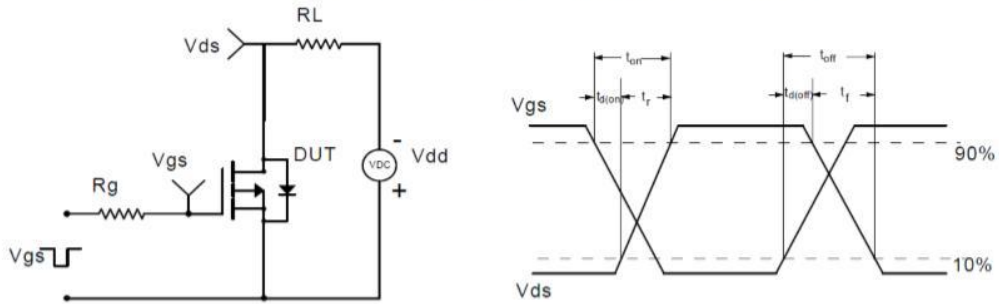


## Test Circuit

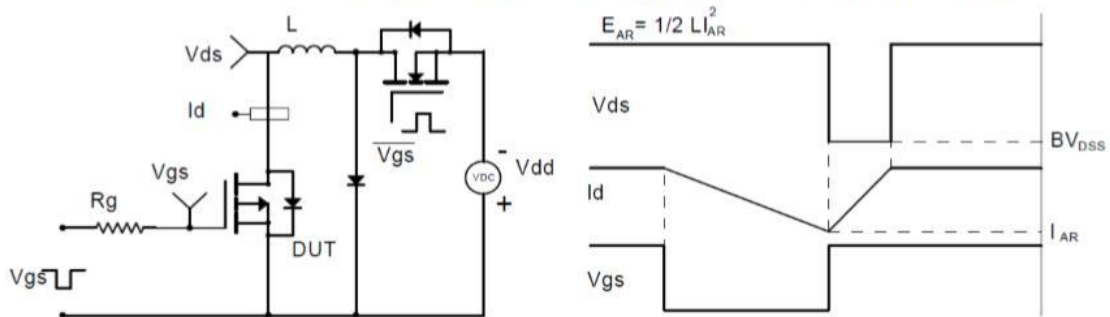
### Gate Charge Test Circuit & Waveform



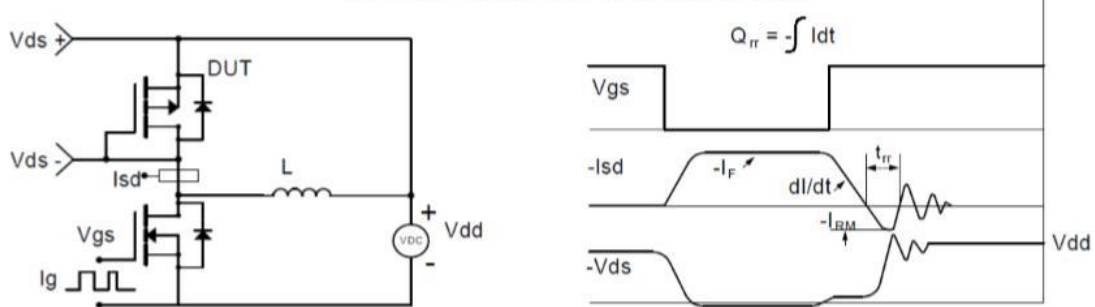
### Resistive Switching Test Circuit & Waveforms



### Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

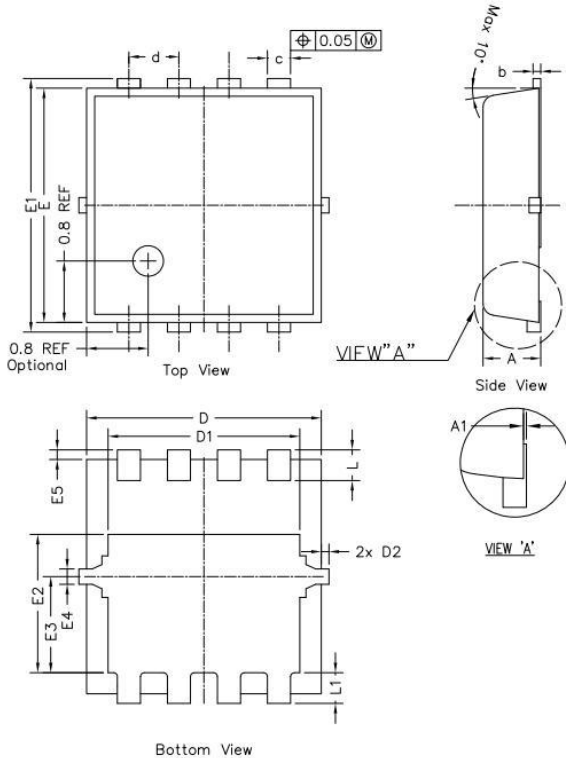


### Diode Recovery Test Circuit & Waveforms





## Package Mechanical Data-PDFN3x3-8L



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	---	---	0.050	----	----	0.002
b	0.144	0.152	0.202	0.006	0.006	0.008
c	0.250	0.300	0.350	0.010	0.012	0.014
d	0.65 BSC			0.026 BSC		
D	2.950	3.050	3.150	0.116	0.120	0.124
D1	2.390	2.490	2.590	0.094	0.098	0.102
D2	---	---	0.125	---	---	0.005
E	2.950	3.050	3.150	0.116	0.120	0.124
E1	3.200	3.300	3.400	0.126	0.130	0.134
E2	1.700	1.800	1.900	0.067	0.071	0.075
E3	1.150	1.250	1.350	0.045	0.049	0.053
E4	0.150	0.200	0.250	0.006	0.008	0.010
E5	0.075	0.125	0.175	0.003	0.005	0.007
L	0.300	0.400	0.500	0.01	0.02	0.02
L1	0.300	0.400	0.500	0.01	0.02	0.02

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